

FIGURE 1

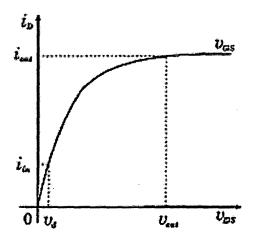


FIGURE 2

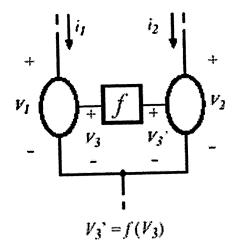


FIGURE 3

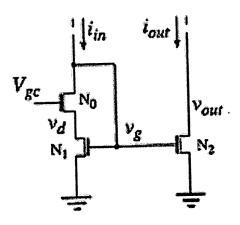


FIGURE 4

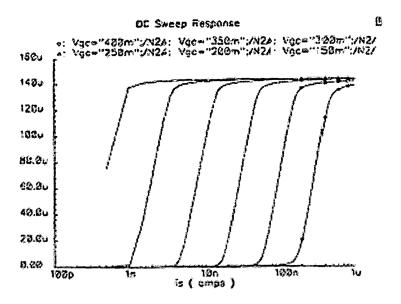


FIGURE 5

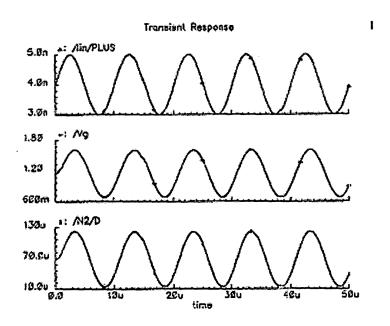


FIGURE 6

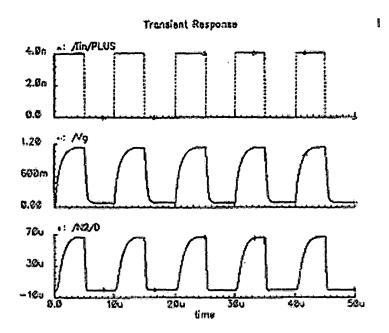


FIGURE 7

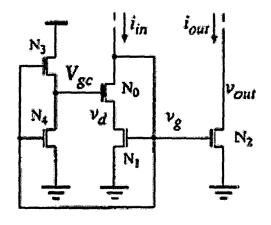


FIGURE 8

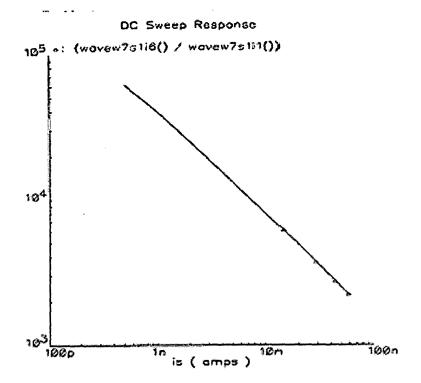
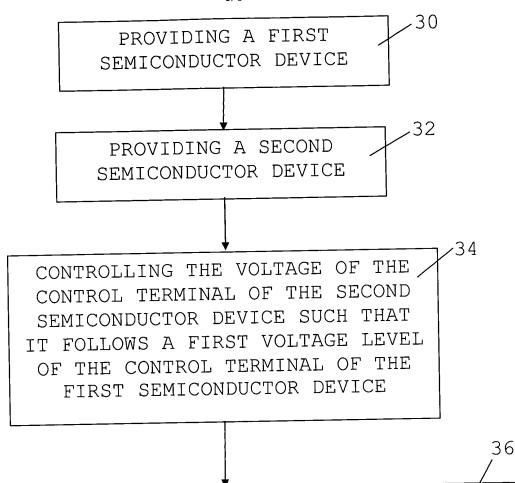


FIGURE 9



PROVIDING CIRCUITRY RESPONSIVE TO THE INPUT
CURRENT SIGNAL TO PROVIDE THE FIRST VOLTAGE
LEVEL SUCH THAT THE FIRST VOLTAGE LEVEL
VARIES WITH THE INPUT CURRENT SIGNAL TO
CAUSE THE SECOND SEMICONDUCTOR DEVICE TO
GENERATE THE OUTPUT CURRENT SIGNAL ACCORDING
TO THE PREDETERMINED GAIN PROFILE, WHEREIN
THE CIRCUITRY BIASES THE FIRST SEMICONDUCTOR
DEVICE IN A FIRST OPERATING REGION, AND
WHEREIN THE SECOND SEMICONDUCTOR DEVICE IS
BIASED IN A SECOND OPERATING REGION HAVING A
HIGHER DEVICE-CURRENT TO CONTROL-VOLTAGE
RATIO THAN THE FIRST OPERATING REGION